

REMARKS

Section A of these Remarks summarizes the status of the pending claims. The remaining sections respond to the rejections and objections of the Office action in the order in which they appeared in the action.

A. Status of Claims:

Claims 1-56 are pending in the application. Claims 45-56 are withdrawn from consideration. Claims 1-3, 6, 8-26, and 35-44 were rejected under 35 USC 102(b) as being anticipated by Feth et al., US Patent No. 4,338,622. Claims 4 and 5 were rejected under 35 USC 103(a) as being unpatentable over Feth et al. in view of Harari, US Patent No. 4,417,325. Claim 7 was rejected under 35 USC 103(a) as being unpatentable over Feth et al.

Claims 27-34 were objected to.

B. 102(b) Rejections: Claims 1-3, 6, 8-26, and 35-44

Claims 1-3, 6, 8-26, and 35-44 were rejected under 35 USC 102(b) as being anticipated Feth et al.

Claim 1 has been cancelled. Claim 2 has been amended to depend from new claim 57. Claim 57 recites a semiconductor device comprising: a silicide layer; a grown dielectric antifuse layer on and in contact with the silicide layer; and a conductive layer or semiconductor layer on and in contact with the grown dielectric antifuse layer, wherein the silicide layer and the grown dielectric antifuse layer are portions of the semiconductor device, and wherein the grown dielectric antifuse layer has suffered dielectric breakdown, such that an electrical connection exists between the silicide layer and the conductive layer or semiconductor layer.

The Examiner identifies element 238 of Fig. 8i of Feth as a grown dielectric layer. The grown dielectric layer of new claim 57 is a dielectric antifuse layer, wherein the grown dielectric antifuse layer has suffered dielectric breakdown, such that an electrical connection exists between the silicide layer and the conductive layer or semiconductor layer. Layer 238 of Feth, however, provides electrical isolation between silicide layer 230 and conductor 252. Feth does not teach or suggest that this layer has suffered dielectric breakdown.

Applicant has shown that Feth et al. do not teach a grown dielectric antifuse layer which has suffered dielectric breakdown such that the silicide layer beneath it and the conductive or semiconductor layer above it are in electrical contact. Claims 2-3, 8-26, and 35-44 all depend from claim 57, and thus also distinguish over the reference. Applicant respectfully requests reconsideration.

C. 103(a) Rejection, Claims 4 and 5

Claims 4 and 5 were rejected under 35 USC 103(a) as being unpatentable over Feth et al. in view of Harari.

Claims 4 and 5 depend from new claim 57 and thus distinguish over the suggested combination for the reasons described in Section B of these remarks. Applicant respectfully requests reconsideration.

D. 103(a) Rejection, Claim 7

Claim 7 was rejected under 35 USC 103(a) as being unpatentable over Feth et al.

Claim 7 depends from new claim 57 and thus distinguishes over the suggested combination for the reasons described in Section B of these remarks. Applicant respectfully requests reconsideration.

E. Claim Objections

Claims 27-34 were objected to as being dependent upon a rejected base claim, but were considered allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

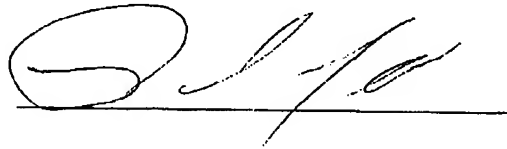
Applicant appreciates the indication of allowable subject matter.

CONCLUSION

In view of these amendments and remarks, Applicant submits that this application is in condition for allowance. Reconsideration is respectfully requested. **To expedite prosecution, Applicant respectfully requests an interview to discuss the references.** If the Examiner has any questions, he is encouraged to contact the undersigned agent at (408) 869-2921.

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Date



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